



SHANGHAI SUNRISE ELECTRONICS CO., LTD.

SB85

SILICON SCHOTTKY
DETECTING DIODE

REVERSE VOLTAGE: 50V

FORWARD CURRENT: 150mA

TECHNICAL
SPECIFICATION

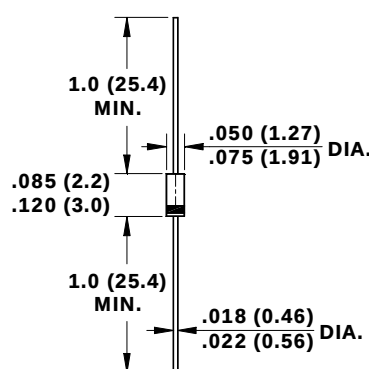
FEATURES

- Small glass structure ensures high reliability
- Fast switching
- Low leakage
- High temperature soldering guaranteed:
250°C/10S/9.5mm lead length
at 5 lbs tension

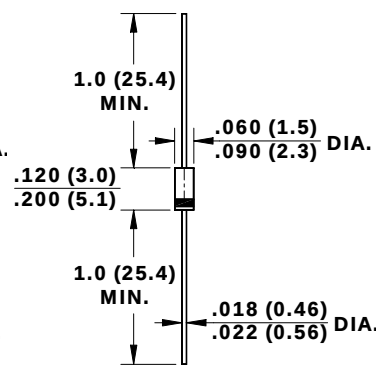
MECHANICAL DATA

- Terminal: Plated axial leads solderable per
MIL-STD 202E, method 208C
- Case: Glass, hermetically sealed
- Polarity: Color band denotes cathode
- Mounting position: Any

DO - 34



DO - 35



Dimensions in inches and (millimeters)

MAXIMUM RATINGS AND CHARACTERISTICS

(Ratings at 25°C ambient temperature unless otherwise specified)

RATINGS		SYMBOL	VALUE		UNITS
			Typ.	Max.	
Reverse Voltage		V_R		50	V
Forward Current (peak)		I_{FM}		150	mA
Forward Current (D.C.)		I_F		30	mA
Forward Voltage (D.C.)	$I_F=10\text{mA}$	V_{F1}		0.4	V
	$I_F=100\text{mA}$	V_{F2}		0.8	V
Reverse Current ($V_R=30\text{V}$)		I_R		3	μA
Capacitance	(Note 1)	C_t	6		pF
Detection Effectiveness	(Note 2)	η	60%		
Operating Junction and Storage Temperature Range		T_J, T_{STG}	-55~+125		°C

Notes:

1. $V_R=10\text{V}$, $f=1\text{MHz}$
2. $V_m=3\text{V(peak)}$, $f=30\text{MHz}$, $R_L=3.9\text{K}\Omega$, $C_t=10\text{pF}$.

<http://www.sse-diode.com>